Ana M Sanchez

List of Publications by Year
in descending order

219 papers	5,689 citations	94433 37 h-index	98798 67 g-index
220 all docs	220 docs citations	220 times ranked	8732 citing authors

#	Article	IF	Citations
1	Lateral heterojunctions within monolayer MoSe2â€“WSe2 semiconductors. Nature Materials, 2014, 13, 1096-1101.	27.5	872
2	A taxonomy for the crossover operator for real-coded genetic algorithms: An experimental study. International Journal of Intelligent Systems, 2003, 18, 309-338.	5.7	301
3	The Peak Pairs algorithm for strain mapping from HRTEM images. Ultramicroscopy, 2007, 107, 1186-1193.	1.9	230
4	Growth of III-nitrides on Si(111) by molecular beam epitaxy Doping, optical, and electrical properties. Journal of Crystal Growth, 1999, 201-202, 296-317.	1.5	189
5	Reducing carrier escape in the InAs/GaAs quantum dot intermediate band solar cell. Journal of Applied Physics, 2010, 108, .	2.5	156
6	Structural reorganization of cylindrical nanoparticles triggered by polylactide stereocomplexation. Nature Communications, 2014, 5, 5746.	12.8	125
7	Physical Vapor Deposition of Metal Nanoparticles on Chemically Modified Graphene: Observations on Metalâ€“Graphene Interactions. Small, 2011, 7, 3202-3210.	10.0	109
8	Room temperature emission at 1.6Î¼m from InGaAs quantum dots capped with GaAsSb. Applied Physics Letters, 2005, 87, 202108.	3.3	106
9	Memetic algorithms based on local search chains for large scale continuous optimisation problems: MA-SSW-Chains. Soft Computing, 2011, 15, 2201-2220.	3.6	88
10	Exploiting nucleobase-containing materials â€“ from monomers to complex morphologies using RAFT dispersion polymerization. Polymer Chemistry, 2015, 6, 106-117.	3.9	79
11	Retarding oxidation of copper nanoparticles without electrical isolation and the size dependence of work function. Nature Communications, 2017, 8, 1894.	12.8	78
12	Weak mismatch epitaxy and structural Feedback in graphene growth on copper foil. Nano Research, 2013, 6, 99-112.	10.4	73
13	A simple approach to characterizing block copolymer assemblies: graphene oxide supports for high contrast multi-technique imaging. Soft Matter, 2012, 8, 3322.	2.7	65
14	Structural analysis of strained quantum dots using nuclear magnetic resonance. Nature Nanotechnology, 2012, 7, 646-650.	31.5	65
15	Artefacts in geometric phase analysis of compound materials. Ultramicroscopy, 2015, 157, 91-97.	1.9	64
16	Low Leakage-Current InAsSb Nanowire Photodetectors on Silicon. Nano Letters, 2016, 16, 182-187.	9.1	63
17	Atomic Defects and Doping of Monolayer NbSe₂. ACS Nano, 2017, 11, 2894-2904.	14.6	63
18	Selenium deficiency in cattle associated with Heinz bodies and anemia. Science, 1984, 223, 491-493.	12.6	62

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19	Wafer-Scale Fabrication of Self-Catalyzed 1.7 eV GaAsP Coreâ€“Shell Nanowire Photocathode on Silicon Substrates. Nano Letters, 2014, 14, 2013-2018.	9.1	58
20	Polarization curling and flux closures in multiferroic tunnel junctions. Nature Communications, 2016, 7, 13484.	12.8	58
21	Bismuth incorporation and the role of ordering in GaAsBi/GaAs structures. Nanoscale Research Letters, 2014, 9, 23.	5.7	56
22	Flexible Memristors Based on Single-Crystalline Ferroelectric Tunnel Junctions. ACS Applied Materials & Interfaces, 2019, 11, 23313-23319.	8.0	56
23	The effect of Si doping on the defect structure of GaN/AlN/Si(111). Applied Physics Letters, 1999, 74, 3362-3364.	3.3	55
24	Design rules for dislocation filters. Journal of Applied Physics, 2014, 116, .	2.5	55
25	Sb-Induced Phase Control of InAsSb Nanowires Grown by Molecular Beam Epitaxy. Nano Letters, 2015, 15, 1109-1116.	9.1	55
26	Highâ€Responsivity Photodetection by a Selfâ€Catalyzed Phaseâ€Pure pâ€GaAs Nanowire. Small, 2018, 14, e1704429.	10.0	54
27	Cubic MnSb: Epitaxial growth of a predicted room temperature half-metal. Physical Review B, 2012, 85, .	3.2	50
28	Influence of Droplet Size on the Growth of Self-Catalyzed Ternary GaAsP Nanowires. Nano Letters, 2016, 16, 1237-1243.	9.1	49
29	Carrier recombination effects in strain compensated quantum dot stacks embedded in solar cells. Applied Physics Letters, 2008, 93, 123114.	3.3	46
30	Origin of Defect Tolerance in InAs/GaAs Quantum Dot Lasers Grown on Silicon. Journal of Lightwave Technology, 2020, 38, 240-248.	4.6	46
31	Structural, magnetic, and transport properties of Fe3O4âˆ•Si(111) and Fe3O4âˆ•Si(001). Journal of Applied Physics, 2007, 101, 123903.	2.5	45
32	Structural analysis of life tested 1.3â€‚Î¼m quantum dot lasers. Journal of Applied Physics, 2008, 103, .	2.5	45
33	Forest cover and deforestation patterns in the Northern Andes (Lake Maracaibo Basin): A synoptic assessment using MODIS and Landsat imagery. Applied Geography, 2012, 35, 152-163.	3.7	44
34	Defect-Free Self-Catalyzed GaAs/GaAsP Nanowire Quantum Dots Grown on Silicon Substrate. Nano Letters, 2016, 16, 504-511.	9.1	42
35	Optical observation of single-carrier charging in type-II quantum ring ensembles. Applied Physics Letters, 2012, 100, .	3.3	41
36	Polarity-Driven Quasi-3-Fold Composition Symmetry of Self-Catalyzed IIIâ€“Vâ€“V Ternary Coreâ€“Shell Nanowires. Nano Letters, 2015, 15, 3128-3133.	9.1	39

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37	Realization of Vertically Aligned, Ultrahigh Aspect Ratio InAsSb Nanowires on Graphite. Nano Letters, 2015, 15, 4348-4355.	9.1	37
38	Direct Fabrication of Functional Ultrathin Single-Crystal Nanowires from Quasi-One-Dimensional van der Waals Crystals. Nano Letters, 2016, 16, 6188-6195.	9.1	37
39	Novel Typeâ€Ⅱ InAs/AlSb Coreâ€“Shell Nanowires and Their Enhanced Negative Photocurrent for Efficient Photodetection. Advanced Functional Materials, 2018, 28, 1705382.	14.9	36
40	Misfit relaxation of InN quantum dots: Effect of the GaN capping layer. Applied Physics Letters, 2006, 88, 151913.	3.3	35
41	An approach to the systematic distortion correction in aberration-corrected HAADF images. Journal of Microscopy, 2006, 221, 1-7.	1.8	34
42	Optical properties of GaN/AlGaN quantum wells grown on nonpolar substrates. Applied Physics Letters, 2008, 93, 101901.	3.3	34
43	Unprecedented New Crystalline Forms of SnSe in Narrow to Medium Diameter Carbon Nanotubes. Nano Letters, 2019, 19, 2979-2984.	9.1	34
44	Ⅲâ€“Ⅴ quantum light source and cavity-QED on Silicon. Scientific Reports, 2013, 3, 1239.	3.3	33
45	Fabrication of crystals from single metal atoms. Nature Communications, 2014, 5, 3851.	12.8	31
46	O-band InAs/GaAs quantum dot laser monolithically integrated on exact (0â€¯0â€¯1) Si substrate. Journal of Crystal Growth, 2019, 511, 56-60.	1.5	31
47	V-defects and dislocations in InGaN/GaN heterostructures. Thin Solid Films, 2005, 479, 316-320.	1.8	30
48	Ferroelectric incommensurate spin crystals. Nature, 2022, 602, 240-244.	27.8	30
49	Incorporation of Sb in InAsâ•GaAs quantum dots. Applied Physics Letters, 2007, 91, 263105.	3.3	29
50	Enhanced infrared photo-response from GaSb/GaAs quantum ring solar cells. Applied Physics Letters, 2012, 101, 231101.	3.3	29
51	Nucleation of InN quantum dots on GaN by metalorganic vapor phase epitaxy. Applied Physics Letters, 2005, 87, 263104.	3.3	28
52	Strain-gradient mediated local conduction in strained bismuth ferrite films. Nature Communications, 2019, 10, 2791.	12.8	28
53	Shape Engineering Driven by Selective Growth of SnO₂ on Doped Ga₂O₃ Nanowires. Nano Letters, 2017, 17, 515-522.	9.1	26
54	Rapidly self-deoxygenating controlled radical polymerization in water via in situ disproportionation of Cu(<scp>i</scp>). Chemical Science, 2020, 11, 5257-5266.	7.4	26

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55	Heterostructure and Q-factor engineering for low-threshold and persistent nanowire lasing. Light: Science and Applications, 2020, 9, 43.	16.6	26
56	Optical polarization anisotropy of a-plane GaN/AlGaN multiple quantum well structures grown on r-plane sapphire substrates. Journal of Applied Physics, 2009, 105, 123112.	2.5	24
57	Antiferroelectric Tunnel Junctions. Advanced Electronic Materials, 2017, 3, 1700126.	5.1	24
58	Doping of Self-Catalyzed Nanowires under the Influence of Droplets. Nano Letters, 2018, 18, 81-87.	9.1	24
59	Electronâ€pumped highâ€efficiency semiconductor laser. Applied Physics Letters, 1986, 49, 546-548.	3.3	23
60	Enhanced Superconductivity in Few-Layer TaS₂ due to Healing by Oxygenation. Nano Letters, 2020, 20, 3808-3818.	9.1	23
61	All-MBE grown InAs/GaAs quantum dot lasers with thin Ge buffer layer on Si substrates. Journal Physics D: Applied Physics, 2021, 54, 035103.	2.8	23
62	Quantitative Strain Mapping Applied to Aberration-Corrected HAADF Images. Microscopy and Microanalysis, 2006, 12, 285-294.	0.4	22
63	Hybrid crossover operators with multiple descendents for real-coded genetic algorithms: Combining neighborhood-based crossover operators. International Journal of Intelligent Systems, 2009, 24, 540-567.	5.7	22
64	Growth of Pure Zinc-Blende GaAs(P) Coreâ€“Shell Nanowires with Highly Regular Morphology. Nano Letters, 2017, 17, 4946-4950.	9.1	22
65	Inversion Boundary Annihilation in GaAs Monolithically Grown on Onâ€Axis Silicon (001). Advanced Optical Materials, 2020, 8, 2000970.	7.3	22
66	Mapping quantum dot-in-well structures on the nanoscale using the plasmon peak in electron energy loss spectra. Physical Review B, 2005, 72, .	3.2	21
67	Real-space observation of ferroelectrically induced magnetic spin crystal in SrRuO3. Nature Communications, 2021, 12, 2007.	12.8	21
68	MBE growth of GaN and AlGaN layers on Si(111) substrates: doping effects. Journal of Crystal Growth, 1999, 201-202, 415-418.	1.5	20
69	Properties of non-polar a-plane GaN/AlGaN quantum wells. Journal of Crystal Growth, 2008, 310, 4983-4986.	1.5	20
70	Growth of ScN epitaxial films by plasma-assisted molecular beam epitaxy. Journal of Crystal Growth, 2009, 311, 2054-2057.	1.5	19
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73	Ten-Fold Enhancement of InAs Nanowire Photoluminescence Emission with an InP Passivation Layer. Nano Letters, 2017, 17, 3629-3633.	9.1	19
74	Highly Strained IIIâ€“Vâ€“V Coaxial Nanowire Quantum Wells with Strong Carrier Confinement. ACS Nano, 2019, 13, 5931-5938.	14.6	19
75	On the Ti₃SiC₂ Metallic Phase Formation for Robust p-Type 4H-SiC Ohmic Contacts. Materials Science Forum, 0, 778-780, 693-696.	0.3	18
76	Realisation of magnetically and atomically abrupt half-metal/semiconductor interface: Co2FeSi0.5Al0.5/Ge(111). Scientific Reports, 2016, 6, 37282.	3.3	18
77	Optimization of self-catalyzed InAs Nanowires on flexible graphite for photovoltaic infrared photodetectors. Scientific Reports, 2017, 7, 46110.	3.3	18
78	Inversion domains and pinholes in GaN grown over Si(111). Applied Physics Letters, 2003, 82, 4471-4473.	3.3	17
79	High-Accuracy Analysis of Nanoscale Semiconductor Layers Using Beam-Exit Ar-Ion Polishing and Scanning Probe Microscopy. ACS Applied Materials & Interfaces, 2013, 5, 3241-3245.	8.0	17
80	Nonradiative Step Facets in Semiconductor Nanowires. Nano Letters, 2017, 17, 2454-2459.	9.1	17
81	Thin Ge buffer layer on silicon for integration of III-V on silicon. Journal of Crystal Growth, 2019, 514, 109-113.	1.5	17
82	Mechanism for pinhole formation in GaNÂˆ•AlNÂˆ•Si(111) layers from steps at the substrate surface. Applied Physics Letters, 2005, 86, 011917.	3.3	16
83	Correlation between defect density and current leakage in InAsÂˆ•GaAs quantum dot-in-well structures. Journal of Applied Physics, 2009, 106, .	2.5	16
84	Blocking of indium incorporation by antimony in IIIâ€“V-Sb nanostructures. Nanotechnology, 2010, 21, 145606.	2.6	16
85	Stable Defects in Semiconductor Nanowires. Nano Letters, 2018, 18, 3081-3087.	9.1	16
86	Growth and Fabrication of Highâ€Quality Single Nanowire Devices with Radial pâ€iâ€n Junctions. Small, 2019, 15, 1803684.	10.0	16
87	High yield production of ultrathin fibroid semiconducting nanowire of Ta2Pd3Se8. Nano Research, 2020, 13, 1627-1635.	10.4	16
88	Toward All-Oxide Magnetic Tunnel Junctions: Epitaxial Growth of SrRuO₃/CoFe₂O₄/La_{2/3}Sr_{1/3}MnO₃ Trilayers. Crystal Growth and Design, 2012, 12, 954-959.	3.0	15
89	Long-Wavelength Photoluminescence from Stacked Layers of High-Quality Type-II GaSb/GaAs Quantum Rings. Crystal Growth and Design, 2013, 13, 1226-1230.	3.0	15
90	Bi-ferroic memristive properties of multiferroic tunnel junctions. Applied Physics Letters, 2018, 112, 102905.	3.3	15

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91	Correlation between spin transport signal and Heusler/semiconductor interface quality in lateral spin-valve devices. Physical Review B, 2018, 98, .	3.2	15
92	Self-Formed Quantum Wires and Dots in GaAsPâ€“GaAsP Coreâ€“Shell Nanowires. Nano Letters, 2019, 19, 4158-4165.	9.1	15
93	Quantum Transport of the 2D Surface State in a Nonsymmorphic Semimetal. Nano Letters, 2021, 21, 4887-4893.	9.1	15
94	Nanoscale EELS analysis ofInGaNâˆ•GaNheterostructures. Physical Review B, 2004, 70, .	3.2	14
95	Strain Relief Analysis of InN Quantum Dots Grown on GaN. Nanoscale Research Letters, 2007, 2, 442-6.	5.7	14
96	Structural and optical changes induced by incorporation of antimony into InAs/GaAs(001) quantum dots. Physical Review B, 2010, 82, .	3.2	14
97	Influence of charged-dislocation density variations on carrier mobility in heteroepitaxial semiconductors: The case of SnO<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mrow /><mml:mn>2</mml:mn></mml:msub></mml:math>on sapphire. Physical Review B, 2012, 86, .	3.2	14
98	Osmium Atoms and Os₂ Molecules Move Faster on Selenium-Doped Compared to Sulfur-Doped Boronic Graphenic Surfaces. Chemistry of Materials, 2015, 27, 5100-5105.	6.7	14
99	Defect-Free Axially Stacked GaAs/GaAsP Nanowire Quantum Dots with Strong Carrier Confinement. Nano Letters, 2021, 21, 5722-5729.	9.1	14
100	Critical thickness of high-temperature AlN interlayers in GaN on sapphire (0001). Journal of Electronic Materials, 2001, 30, L17-L20.	2.2	13
101	A mechanism for the multiple atomic configurations of inversion domain boundaries in GaN layers grown on Si(111). Applied Physics Letters, 2001, 79, 3588-3590.	3.3	13
102	The effect of atomic structure on interface spin-polarization of half-metallic spin valves: Co2MnSi/Ag epitaxial interfaces. Applied Physics Letters, 2015, 107, .	3.3	13
103	Nanomaterials of the Topological Crystalline Insulators, Pb_{1â€“x}Sn_xTe and Pb_{1â€“x}Sn_xSe. Crystal Growth and Design, 2015, 15, 5202-5206.	3.0	13
104	Comparative Study of RESURF Si/SiC LDMOSFETs for High-Temperature Applications Using TCAD Modeling. IEEE Transactions on Electron Devices, 2017, 64, 3713-3718.	3.0	13
105	Inversion domains in GaN layers grown on (111) silicon by molecular-beam epitaxy. Applied Physics Letters, 2001, 78, 2688-2690.	3.3	12
106	Direct experimental evidence of metastable epitaxial zinc-blende MgS. Applied Physics Letters, 2006, 89, 121907.	3.3	12
107	Configuration of the misfit dislocation networks in uncapped and capped InN quantum dots. Applied Physics Letters, 2007, 91, 071915.	3.3	12
108	Ferroelectric parallel-plate capacitors with copper electrodes for high-frequency applications. Applied Physics Letters, 2007, 91, 252902.	3.3	12

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109	Strain Mapping at the Atomic Scale in Highly Mismatched Heterointerfaces. Advanced Functional Materials, 2007, 17, 2588-2593.	14.9	12
110	A new approach to high resolution, high contrast electron microscopy of macromolecular block copolymer assemblies. Soft Matter, 2013, 9, 3741.	2.7	12
111	Effect of annealing in the Sb and In distribution of type II GaAsSb-capped InAs quantum dots. Semiconductor Science and Technology, 2015, 30, 114006.	2.0	12
112	Quantitative Highâ€Dynamicâ€Range Electron Diffraction of Polar Nanodomains in Pb₂ScTaO₆. Advanced Materials, 2019, 31, e1806498.	21.0	12
113	Emergent Antipolar Phase in BiFeO₃â€“La_{0.7}Sr_{0.3}MnO₃ Superlattice. Nano Letters, 2020, 20, 6045-6050.	9.1	12
114	Robust Protection of IIIâ€“V Nanowires in Water Splitting by a Thin Compact TiO₂ Layer. ACS Applied Materials & Interfaces, 2021, 13, 30950-30958.	8.0	12
115	Electron microscopy study of SiC obtained by the carbonization of Si(111). Thin Solid Films, 1999, 343-344, 305-308.	1.8	11
116	Structural, optical, and electrical properties of AgIn5Te8. Journal of Applied Physics, 2005, 97, 053505.	2.5	11
117	Graphitic platform for self-catalysed InAs nanowires growth by molecular beam epitaxy. Nanoscale Research Letters, 2014, 9, 321.	5.7	11
118	Room-Temperature Mid-Infrared Emission from Faceted InAsSb Multi Quantum Wells Embedded in InAs Nanowires. Nano Letters, 2018, 18, 235-240.	9.1	11
119	Fully in situ Nb/InAs-nanowire Josephson junctions by selective-area growth and shadow evaporation. Nanoscale Advances, 2021, 3, 1413-1421.	4.6	11
120	Selfâ€catalysed growth of InAs nanowires on bare Si substrates by droplet epitaxy. Physica Status Solidi - Rapid Research Letters, 2014, 8, 658-662.	2.4	10
121	Quantum dots in strained layersâ€”preventing relaxation through the precipitate hardening effect. Journal of Applied Physics, 2008, 104, .	2.5	9
122	Relaxation dynamics and residual strain in metamorphic AlSb on GaAs. Applied Physics Letters, 2012, 100, .	3.3	9
123	The antiphase boundary in half-metallic Heusler alloy Co2Fe(Al,Si): atomic structure, spin polarization reversal, and domain wall effects. Applied Physics Letters, 2016, 109, .	3.3	9
124	InAs/GaAs quantum dot solar cells with quantum dots in the base region. IET Optoelectronics, 2019, 13, 215-217.	3.3	9
125	Engineering the Side Facets of Vertical [100] Oriented InP Nanowires for Novel Radial Heterostructures. Nanoscale Research Letters, 2019, 14, 399.	5.7	9
126	Zn₂GeO₄/SnO₂ Nanowire Heterostructures Driven by Plateauâ€“Rayleigh Instability. Crystal Growth and Design, 2020, 20, 506-513.	3.0	9

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127	Vibrational and electronic structures of tin selenide nanowires confined inside carbon nanotubes. Synthetic Metals, 2022, 284, 116968.	3.9	9
128	High temperature AlN intermediate layer in GaN grown by molecular beam epitaxy. Journal of Crystal Growth, 2000, 216, 15-20.	1.5	8
129	AlN buffer layer thickness influence on inversion domains in GaN/AlN/Si(111). Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2002, 93, 181-184.	3.5	8
130	Structural characterization of InN quantum dots grown by Metalorganic Vapour Phase Epitaxy. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 1687-1690.	0.8	8
131	Real-parameter crossover operators with multiple descendents: An experimental study. International Journal of Intelligent Systems, 2008, 23, 246-268.	5.7	8
132	Structural, optical and vibrational properties of self-assembled Pbn+1(Ti1â^'xFex)nO3n+1â^'Î´ Ruddlesden-Popper superstructures. Scientific Reports, 2015, 5, 7719.	3.3	8
133	Optimisation of anatase TiO2 thin film growth on LaAlO3(0 0 1) using pulsed laser deposition. Applied Surface Science, 2016, 388, 684-690.	6.1	8
134	Preferred growth direction of IIIâ€“V nanowires on differently oriented Si substrates. Nanotechnology, 2020, 31, 475708.	2.6	8
135	Nanometer-scale strain measurements in semiconductors: An innovative approach using the plasmon peak in electron energy loss spectra. Applied Physics Letters, 2006, 88, 051917.	3.3	7
136	Anomalous magnetic field effects during pulsed injection metal-organic chemical vapor deposition of magnetite films. Applied Physics Letters, 2010, 96, .	3.3	7
137	Photoluminescence of InAs0.926Sb0.063N0.011/InAs multi-quantum wells in the mid-infrared spectral range. Journal Physics D: Applied Physics, 2010, 43, 345103.	2.8	7
138	Optimal growth and thermal stability of crystalline Be0.25Zn0.75O alloy films on Al2O3(0001). Applied Physics Letters, 2014, 104, .	3.3	7
139	Coexistence of optically active radial and axial CdTe insertions in single ZnTe nanowire. Nanoscale, 2016, 8, 5720-5727.	5.6	7
140	Polarization Screening Mechanisms at La_{0.7}Sr_{0.3}MnO₃â€“PbTiO₃ Interfaces. ACS Applied Materials & Interfaces, 2020, 12, 10657-10663.	8.0	7
141	Atomic and electronic structure of two-dimensional Mo_{(1â^'} _x)W _x S₂ alloys. JPhys Materials, 2021, 4, 025004.	4.2	7
142	Properties of Homoepitaxial and Heteroepitaxial GaN Layers Grown by Plasma-Assisted MBE. Physica Status Solidi A, 1999, 176, 447-452.	1.7	6
143	Interfacial steps, dislocations, and inversion domain boundaries in the GaN/AlN/Si (0001)/(111) epitaxial system. Physica Status Solidi (B): Basic Research, 2005, 242, 1617-1627.	1.5	6
144	Morphology â€“ composition correlations in carbon nanotubes synthesised with nitrogen and phosphorus containing precursors. Physical Chemistry Chemical Physics, 2015, 17, 2137-2142.	2.8	6

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145	Nanoscale Inhomogeneous Superconductivity in Fe(Te1â€“xSex) Probed by Nanostructure Transport. ACS Nano, 2016, 10, 429-435.	14.6	6
146	3D and 2D growth of SnO₂ nanostructures on Ga₂O₃ nanowires: synthesis and structural characterization. CrystEngComm, 2017, 19, 6127-6132.	2.6	6
147	Hybrid IIIâ€“V/IV Nanowires: High-Quality Ge Shell Epitaxy on GaAs Cores. Nano Letters, 2018, 18, 6397-6403.	9.1	6
148	Growth and characterisation of MnSb(0â€¯0â€¯0â€¯1)/InGaAs(1â€¯1â€¯1)A epitaxial films. Journal of Crystal Growth, 2018, 498, 391-398.	1.5	6
149	Influence of Si Doping on the Subgrain Structure of GaN Grown on AlN/Si(111). Physica Status Solidi A, 1999, 176, 401-406.	1.7	5
150	Electron tomography of IIIâ€V quantum dots using dark field 002 imaging conditions. Journal of Microscopy, 2010, 237, 148-154.	1.8	5
151	A test for the homoscedasticity of the residuals in fuzzy rule-based forecasters. Applied Intelligence, 2011, 34, 386-393.	5.3	5
152	Bow Free 4'' Diameter 3C-SiC Epilayers Formed upon Wafer-Bonded Si/SiC Substrates. ECS Solid State Letters, 2012, 1, P85-P88.	1.4	5
153	EPITAXIAL GROWTH OF CUBIC MnSb ON GaAs AND InGaAs(111). Spin, 2014, 04, 1440025.	1.3	5
154	Growth of complex SiGe/Ge superlattices by reduced pressure chemical vapour deposition at low temperature. Semiconductor Science and Technology, 2015, 30, 114009.	2.0	5
155	Si1-x Ge x /Si Interface Profiles Measured to Sub-Nanometer Precision Using uleSIMS Energy Sequencing. Journal of the American Society for Mass Spectrometry, 2016, 27, 1694-1702.	2.8	5
156	Control of complex quantum structures in droplet epitaxy. Semiconductor Science and Technology, 2019, 34, 095011.	2.0	5
157	Defect Dynamics in Self-Catalyzed IIIâ€“V Semiconductor Nanowires. Nano Letters, 2019, 19, 4574-4580.	9.1	5
158	Ge incorporation in gallium oxide nanostructures grown by thermal treatment. Journal of Materials Science, 2020, 55, 11431-11438.	3.7	5
159	Self-Catalyzed AlGaAs Nanowires and AlGaAs/GaAs Nanowire-Quantum Dots on Si Substrates. Journal of Physical Chemistry C, 2021, 125, 14338-14347.	3.1	5
160	Structural characterization of high temperature AlN intermediate layer in GaN grown by molecular beam epitaxy. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2001, 80, 299-303.	3.5	4
161	Origin of Inversion Domains in GaN/AlN/Si(111) Heterostructures Grown by Molecular Beam Epitaxy. Physica Status Solidi (B): Basic Research, 2002, 234, 935-938.	1.5	4
162	Disconnections and inversion domain formation in GaN/AlN heteroepitaxy on (111) silicon. Physica Status Solidi C: Current Topics in Solid State Physics, 2005, 2, 2500-2503.	0.8	4

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163	Theoretical modelling of quaternary GaInAsSb/GaAs self-assembled quantum dots. Journal of Physics: Conference Series, 2010, 245, 012081.	0.4	4
164	Structural characterization of GaSb-capped InAs/GaAs quantum dots with a GaAs intermediate layer. Materials Letters, 2011, 65, 1608-1610.	2.6	4
165	Quantitative study of the interfacial intermixing and segregation effects across the wetting layer of Ga(As,Sb)-capped InAs quantum dots. Applied Physics Letters, 2012, 101, .	3.3	4
166	Rapid thermal annealing and photoluminescence of type-II GaSb single monolayer quantum dot stacks. Journal Physics D: Applied Physics, 2013, 46, 305104.	2.8	4
167	Bipolar Conduction across a Wafer Bonded p-n Si/SiC Heterojunction. Materials Science Forum, 0, 740-742, 1006-1009.	0.3	4
168	The Effect of Interfacial Charge on the Development of Wafer Bonded Silicon-on-Silicon-Carbide Power Devices. Materials Science Forum, 0, 897, 747-750.	0.3	4
169	Hard-Gap Spectroscopy in a Self-Defined Mesoscopic<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline" overflow="scroll"><mml:mrow><mml:mi>In</mml:mi><mml:mi>As</mml:mi></mml:mrow></mml:math>/<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline" overflow="scroll"><mml:mi>Al</mml:mi></mml:math>Nanowire Josephson Junction. Physical Review Applied, 2020, 14, .	3.8	4
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